

SOLITRON DEVICES INC

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ENGINEERING DEVICE SPECIFICATION

NO. 6079/2N2634

SILICON TRANSISTOR

查询"2N2634"供应商

GENERAL DESCRIPTION

This device is an NPN Triple Diffused Planar Power Transistor packaged in a double-ended stud-mounted case.

DESIGN LIMITS

Outline DR 4585

Storage Temperature, T_{stg}

Operating Junction Temperature

Collector Current

Base Current

Continuous Power Dissipation at 100°C

Thermal Resistance

-65°C to 200°C

175°C

5 A Max.

.5 A Max.

20 Watts

3.75°C/W

PERFORMANCE CHARACTERISTICS, $T_C = 25 \pm 3^\circ\text{C}$ (unless noted)

Symbol	Condition	Limit
BV _{CB0}	$I_{CB0} = 10 \mu\text{A}$	150 V Min.
BV _{EB0}	$I_{EB0} = 10 \mu\text{A}$	8 V Min.
BV _{CEO}	$I_{CEO} \leq 10 \text{ MA}$	100 V Min.
I_{CEX}	$V_{CE} = 60 \text{ V}$, $V_{EB} = 0.5 \text{ V}$, $T_C = 150^\circ\text{C}$	50 μA Max.
I_{CEX}	$V_{CE} = 150 \text{ V}$, $V_{EB} = 0.5 \text{ V}$	10 μA Max.
I_{CB0}	$V_{CB} = 60 \text{ V}$	0.1 μA Max.
I_{EB0}	$V_{EB} = 8 \text{ V}$	10 μA Max.
I_{EB0}	$V_{EB} = 5 \text{ V}$	0.1 μA Max.
$V_{CEO}(\text{sust})$	$I_C = 100 \text{ MA}$, $I_B = 0$	90 V Min.
I_{CEO}	$V_{CE} = 50 \text{ V}$, $I_B = 0$	100 μA Max.
h_{FE}	$I_C = 10 \text{ MA}$, $V_{CE} = 2 \text{ V}^*$	30 Min.
h_{FE}	$I_C = 1 \text{ A}$, $V_{CE} = 2 \text{ V}^*$	40 - 120
h_{FE}	$I_C = 1 \text{ A}$, $V_{CE} = 2 \text{ V}$, $T_C = -55^\circ\text{C}^*$	10 Min.
h_{FE}	$I_C = 5 \text{ A}$, $V_{CE} = 5 \text{ V}^*$	15 Min.
$V_{CE}(\text{Sat})$	$I_C = 1.0 \text{ A}$, $I_B = 100 \text{ MA}^*$	.25 V Max.
$V_{CE}(\text{Sat})$	$I_C = 5 \text{ A}$, $I_B = 500 \text{ MA}^*$	2.0 V Max.
$V_{BE}(\text{Sat})$	$I_C = 1.0 \text{ A}$, $I_B = 100 \text{ MA}^*$	1.2 V Max.
$V_{BE}(\text{Sat})$	$I_C = 1.0 \text{ A}$, $V_{CE} = 2 \text{ V}^*$	1.2 V Max.

* Pulsed 330 μs , 2% duty cycle, sq. wave

A

Corrected to
registration

11/2/62

MA

MINNEAPOLIS-HONEYWELL REGULATOR CO

RIVIERA BEACH, FLORIDA

FOR

SILICON TRANSISTOR

DATE 10/5/62 DRWN. mmm

CHKD.

APPD.

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ENGINEERING DEVICE SPECIFICATION

NO. 6079/2N2634
SILICON TRANSIST

查询"2N2634"供应商

Symbol	Condition	Limit
h_{fe}	$I_C = 1.0 \text{ A}, V_{CE} = 10 \text{ V}, f = 10 \text{ MC}$	2 Min.
h_{fe}	$I_C = 50 \text{ MA}, V_{CE} = 5 \text{ V}, f = 1 \text{ KC.}$	40 - 140
C_{ob}	$I_C = 0, V_{CB} = 10 \text{ V}, f = 1 \text{ MC}$	150 pf
t_r	(Appendix A)	80 ns
t_s	(Appendix A)	60 ns
t_f	(Appendix A)	80 ns

MINNEAPOLIS-HONEYWELL REGULATOR
RIVIERA BEACH, FLORIDAFOR
SILICON TRANSISTOR

DATE 10/4/62 DRWN. mmm

CHKD.

APPD. *JBM*

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REVISION

DATE

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